

DEPARTMENT OF PHYSICS AND NANOTECHNOLOGY SRM INSTITUTE OF SCIENCE AND TECHNOLOGY

Module-IV Lecture-8

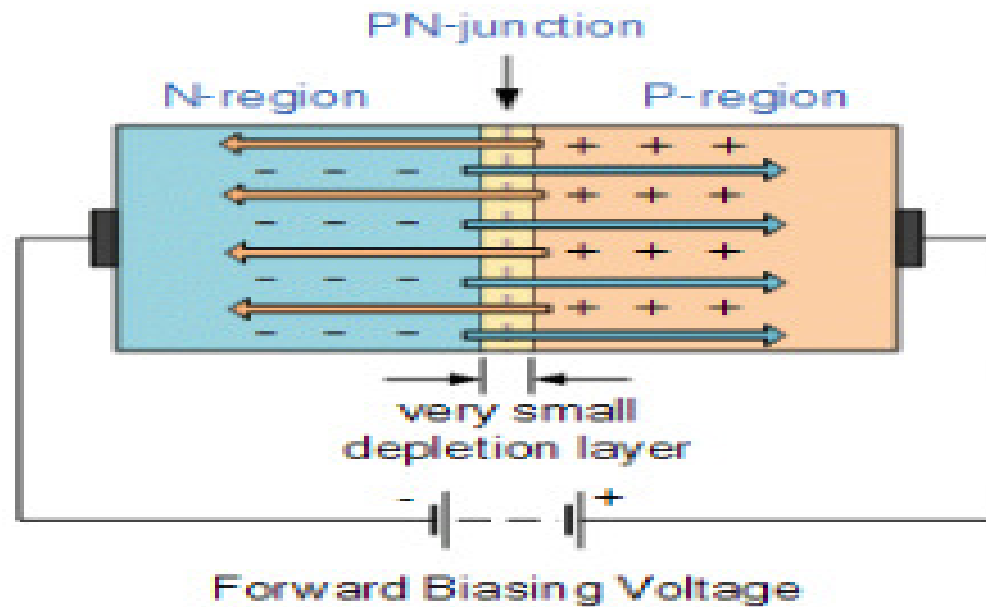
Extraction Parameters & I-V Characteristic of PN Junction Diode

PN Junction Diode

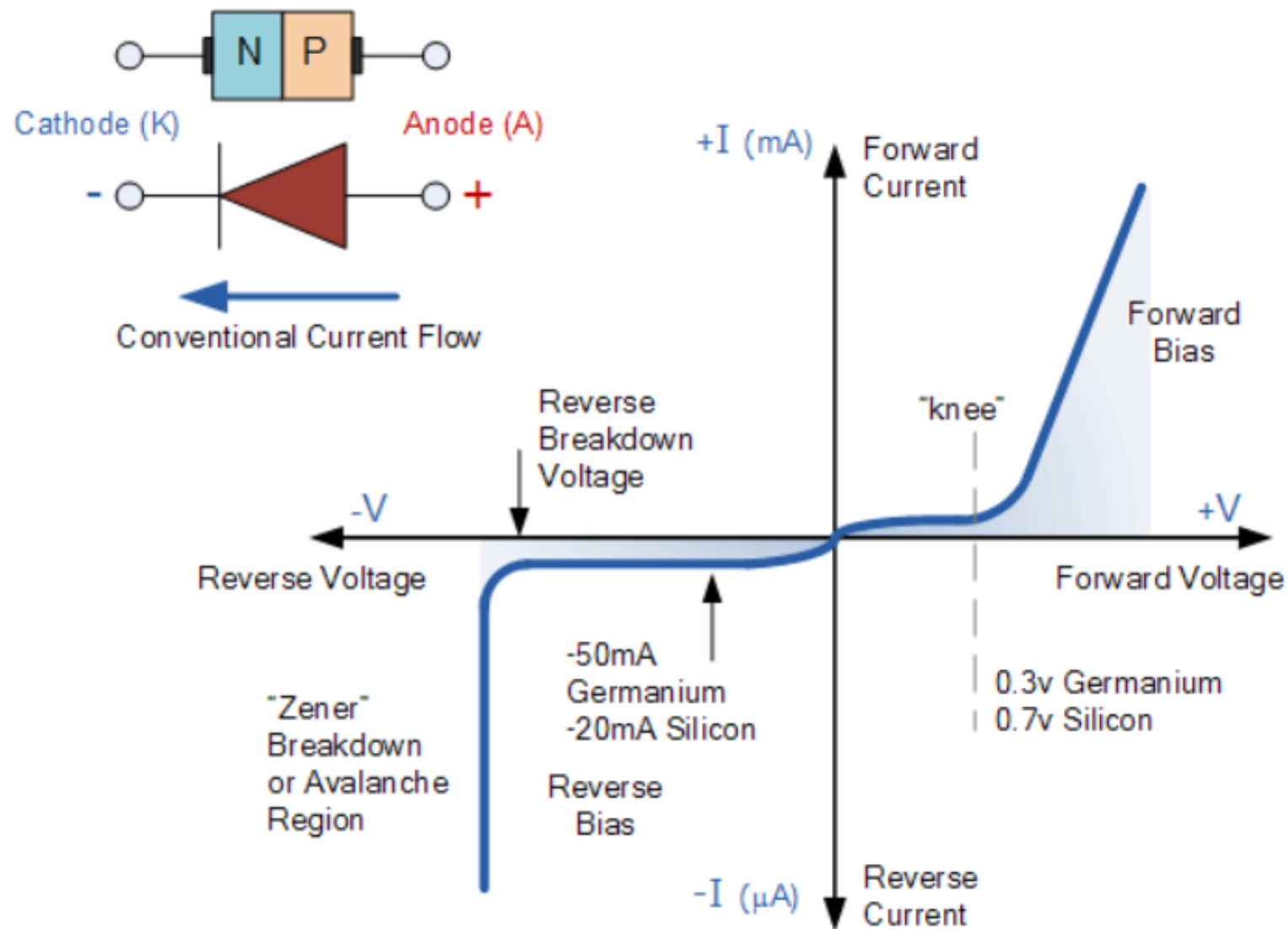
- if we join P-type and N-type semiconductor materials together they behave in a very different way and producing what is generally known as a “**PN Junction**”.
- The charge transfer of electrons and holes across the PN junction is known as **diffusion**. The width of these P and N layers depends on how heavily each side is doped with acceptor density N_A , and donor density N_D , respectively.
- Due to diffusion processes **potential barrier** is formed around the area of the junction as the donor atoms repel the holes and the acceptor atoms repel the electrons.
- At room temperature the voltage across the depletion layer for silicon is about 0.6 – 0.7 volts and for germanium is about 0.3 – 0.35 volts. This potential barrier will always exist even if the device is not connected to any external power source, as seen in diodes.

I-V Characteristics in a Diode

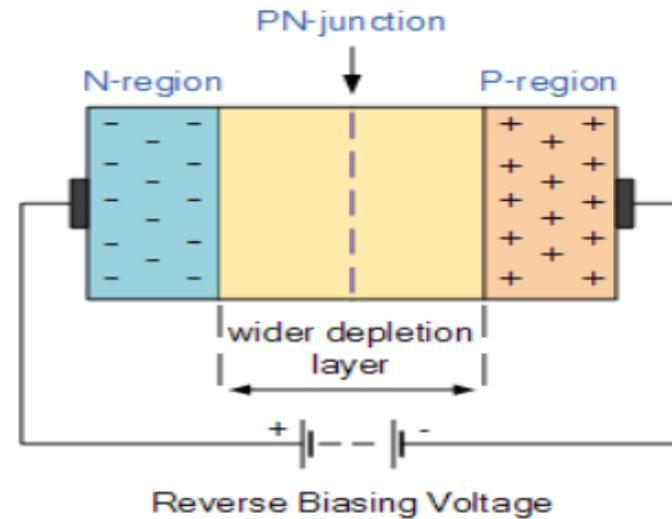
- A *PN Junction Diode* is one of the simplest semiconductor devices around, and which has the characteristic of passing current in only one direction only. However, unlike a resistor, a diode does not behave linearly with respect to the applied voltage as the diode has an exponential current-voltage (I-V) relationship and therefore we can not described its operation by simply using an equation such as Ohm's law.
- If a suitable positive voltage (forward bias) is applied between the two ends of the PN junction, it can supply free electrons and holes with the extra energy they require to cross the junction as the width of the depletion layer around the PN junction is decreased.
- By applying a negative voltage (reverse bias) results in the free charges being pulled away from the junction resulting in the depletion layer width being increased. This has the effect of increasing or decreasing the effective resistance of the junction itself allowing or blocking current flow through the diode.



➤ When a diode is connected in a **Forward Bias** condition, a negative voltage is applied to the N-type material and a positive voltage is applied to the P-type material. If this external voltage becomes greater than the value of the potential barrier, approx. 0.7 volts for silicon and 0.3 volts for germanium, the potential barriers opposition will be overcome and current will start to flow.



- Due to forward biasing the negative voltage pushes or repels electrons towards the junction giving them the energy to cross over and combine with the holes being pushed in the opposite direction towards the junction by the positive voltage. This results in a characteristics curve of zero current flowing up to this voltage point, called the “**knee**” on the static curves and then a high current flow through the diode with little increase in the external voltage.
- The point at which this sudden increase in current takes place is represented on the static I-V characteristics curve above as the “knee” point.
- Since the diode can conduct “infinite” current above this knee point as it effectively becomes a short circuit, therefore resistors are used in series with the diode to limit its current flow. Exceeding its maximum forward current specification causes the device to dissipate more power in the form of heat than it was designed for resulting in a very quick failure of the device.



- When a diode is connected in a **Reverse Bias** condition, a positive voltage is applied to the N-type material and a negative voltage is applied to the P-type material.
- The net result is that the depletion layer grows wider due to a lack of electrons and holes and presents a high impedance path, almost an insulator. The result is that a high potential barrier is created thus preventing current from flowing through the semiconductor material.

- This condition represents a high resistance value to the PN junction and practically zero current flows through the junction diode with an increase in bias voltage. However, a very small **leakage current** does flow through the junction which can be measured in micro-amperes, (μA).
- if the reverse bias voltage applied to the diode is increased to a sufficiently high enough value, it will cause the diode's PN junction to overheat and fail due to the avalanche effect around the junction. This may cause the diode to become shorted and will result in the flow of maximum circuit current, and this shown as a step downward slope in the reverse static characteristics curve below.
- When the reverse voltage is increased beyond the limit, then the reverse current increases drastically. This particular voltage that causes the drastic change in reverse current is called **Reverse Breakdown voltage**. Diode breakdown occurs by two mechanisms: Avalanche breakdown and Zener breakdown.